

Supporting Information

Energy harvesting from $\text{NiCo}_2\text{S}_4/\text{Co}_x\text{S}_y$ nanoflakes: Two-fold strategy by morphology control & redox additive electrolyte

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S1: Characterization details

A Horiba Jobin–Yvon Raman spectrometer with a 633 nm excitation laser was used to record the Raman spectrum of all the electrodes. A Rigaku X-ray diffractometer (Cu K_{α} radiation of 1.54 Å wavelength) was used for X-ray diffraction (XRD) of all the electrodes. A Supra 55 Zeiss scanning electron microscopy (SEM) was used for surface morphology and elemental distribution X-ray (EDX) mapping of all the electrodes. Instrument: X-ray photoelectron spectroscopy (XPS, PHI 5000 VersaProbe II, ULVAC-PHI Inc., USA) equipped with micro-focused (100 μm , 15 kV) monochromatic Al- K_{α} X-Ray source ($h\nu = 1486.6\text{ eV}$). Both survey spectra and narrow scans (high-resolution spectra) were recorded. Survey scans were recorded with an X-ray source power of 50W and pass energy of 187.85 eV. High-resolution spectra of the major elements were recorded at 46.95 eV pass energy. XPS data were processed using PHI's Multipak software. The binding energy was referenced to the C 1s peak at 284.8 eV.. A Metrohm-Multi Autolab M204 potentiostat was used for deposition and the device's electrochemical measurements.

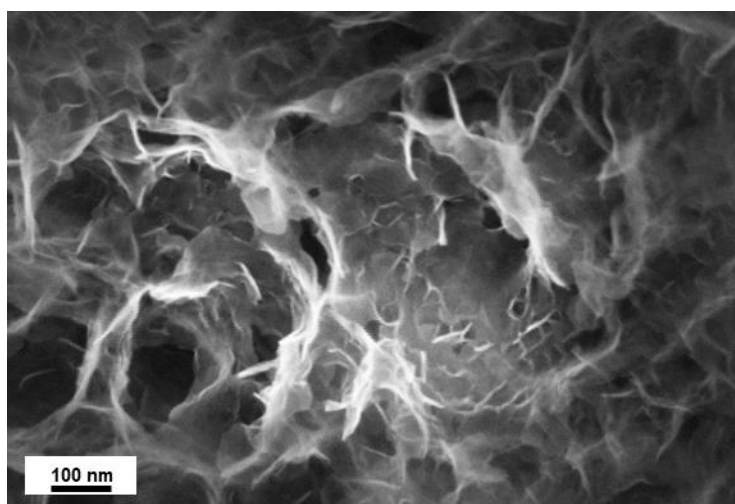


Figure S1: High magnification SEM image of NCS/CS.

Table S1: Chemical composition of the NCS/CS complex over CC.

S.No	Atom	Percentage Contribution (%)
1	Ni	8.35
2	Co	26.51
3	S	45.83

S2: Electrochemical measurements of electrode

The electrochemical properties of electrodes were investigated using the conventional three-electrode system, with electroactive material $\text{NiCo}_2\text{S}_4/\text{Co}_x\text{S}_y$ (NCS/CS) as the working electrode, Pt wire as a counter electrode, and Ag/AgCl as a reference electrode in 1 M KOH with or without 0.05 M $\text{K}_3[\text{Fe}(\text{CN})_6]$ in 20 ml DI as electrolyte. The cyclic voltammetry (CV) curves were obtained at several scan rates (5 to 50 mV/s), within a wide potential range of -0.1 V to 0.7 V. The electrochemical impedance spectroscopy of electrodes was done within the frequency range of 10 kHz to 10 mHz at 0.4 V. Galvanostatic charge-discharge (GCD) cycles were obtained at various current densities (1.0 A/g to 10 A/g) within the wide potential window of -0.1 V to 0.45 V.

The specific capacitance of the electrode is calculated in GCD plots using the equation^{S1} as below-

$$C_s = \frac{I\Delta t_d}{A\Delta V} (F/cm^2), \text{ or } C_s = \frac{I\Delta t_d}{m\Delta V} (F/g), \quad (\text{S1})$$

where Δt_d is the discharging time, ΔV is the potential window of the GCD plot, and I/A or I/m is the current density of electrode materials on CC (A is the active area of electrode: 1.5 cm^2 in this case, and m is the mass of active material: 1.5 mg in this case.).

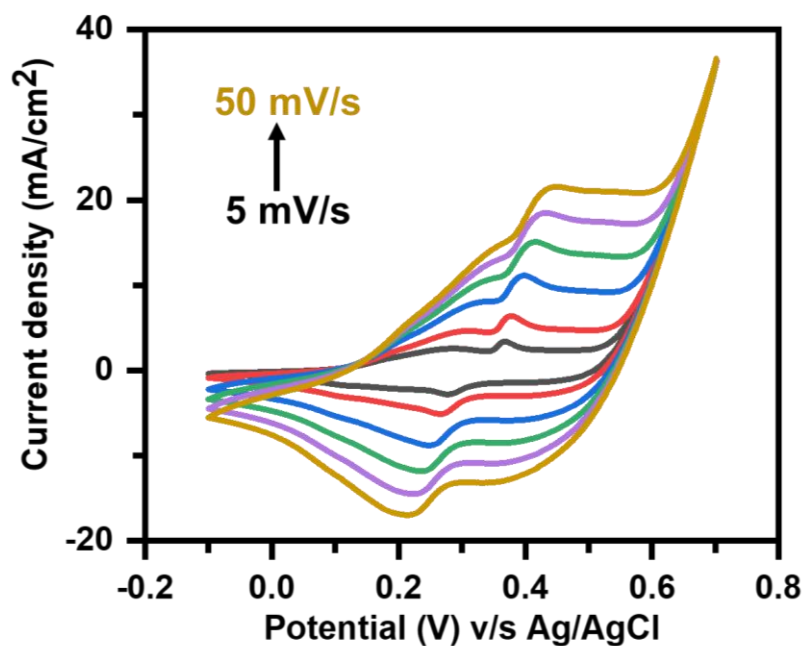


Figure S2: CV cure of NiCo2S4/CoxSy in 1 M KOH at various scan rates.

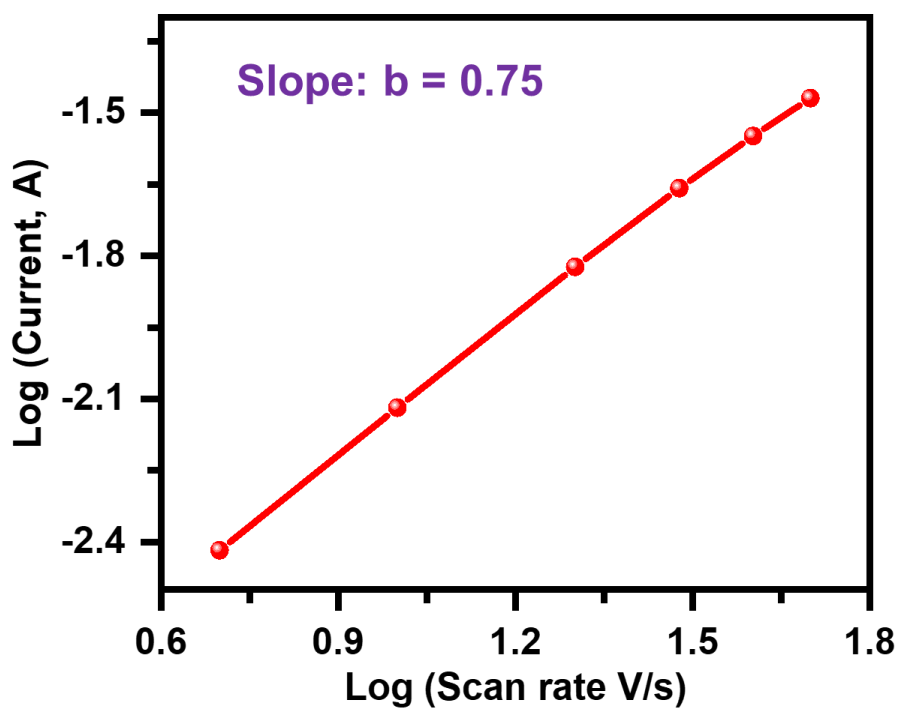


Figure S3: Variation of logarithmic peak current as a function of logarithmic scan rate for NCS/CS electrode in 1 KOH electrolyte.

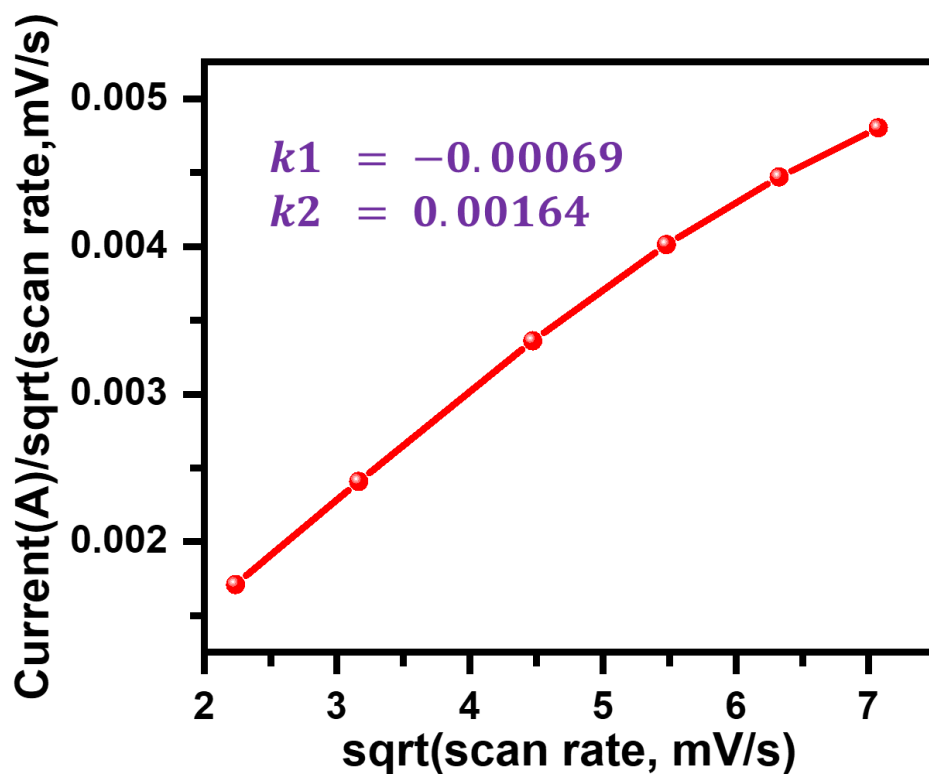


Figure S4: Variation of current/ $\sqrt{\text{scan rate}}$ as a function of $\sqrt{\text{scan rate}}$ for NCS/CS electrode in 1 KOH electrolyte.

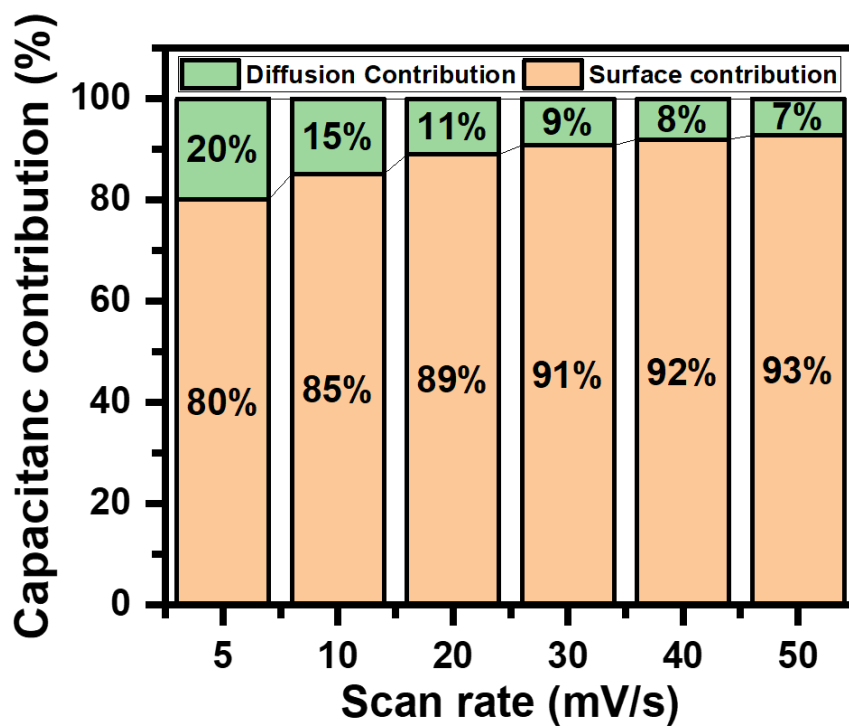


Figure S5: Capacitance contribution graph of NCS/CS electrodes in 1 KOH electrolyte.

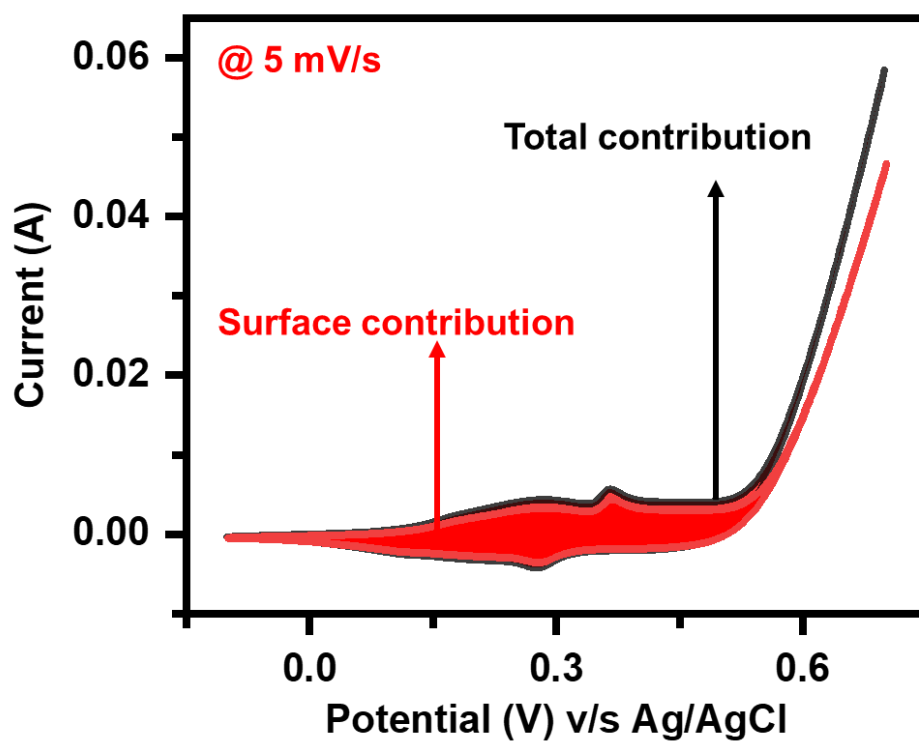


Figure S6: Pictorial representation of dominance of surface-controlled contribution for NCS/CS in 1 M KOH electrolyte at 5 mV/s.

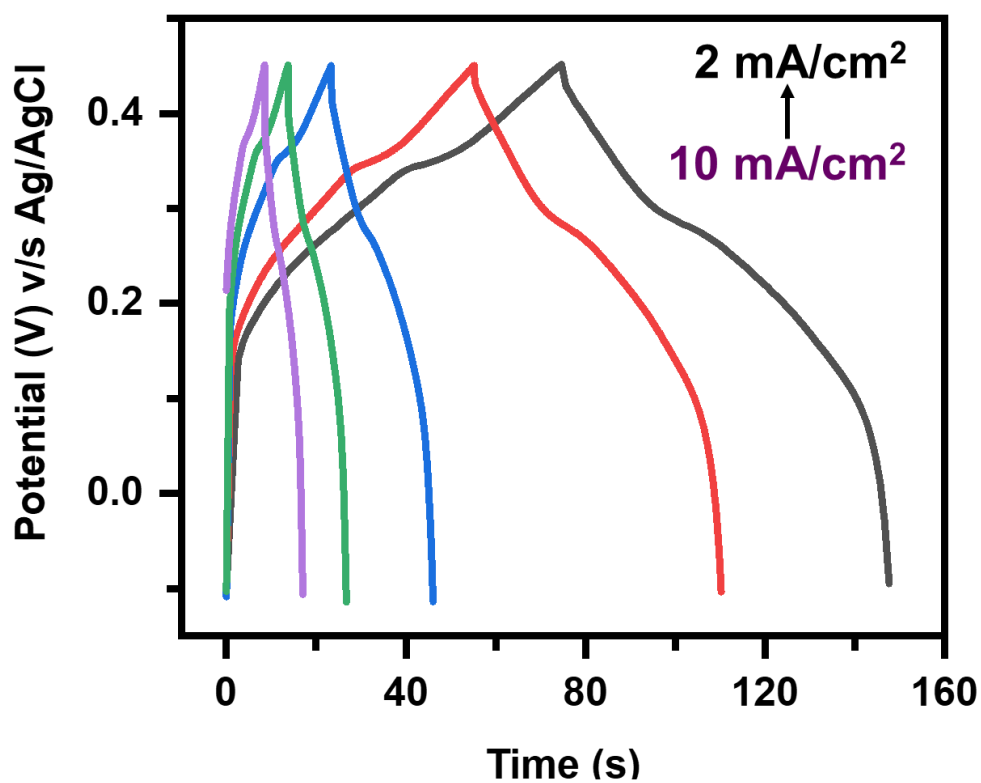


Figure S7: GCD plot of NNCS/CS electrodes in 1 M KOH electrolyte at various current densities.

Table S2: Specific capacitance comparison table for NiCo₂S₄/CS electrode and their composites with already reported literature.

S.No	Material	Specific capacitance	Current Density	Reference
1	graphene oxide-NiCo ₂ S ₄	1640 F/g	1A/g	Panicker et al. ¹
2	NiCo ₂ S ₄ @NiMoO ₄ /NF	2006 F g ⁻¹	5 mA cm ⁻²	Zhang et al. ²
3	NiCo ₂ S ₄ nano-petals	2036.5 F g ⁻¹	1 A g ⁻¹	Wen et al. ³
4	NiCo ₂ S ₄ urchin balls	1352.2 F g ⁻¹	1 A g ⁻¹	Tian et al. ⁴
5	FCP@ NiCo ₂ S ₄	3115 mF cm ⁻²	2 mA cm ⁻²	Wu et al. ⁵
6	NiCo ₂ S ₄ @PPy	1524 F g ⁻¹	4 mA cm ⁻¹	Meng et al. ⁶
7	V/MWCNTs	2080 F g ⁻¹	1 A g ⁻¹	Sajjad et al. ⁷
8	NiCo ₂ S ₄ /CNT	2210 F g ⁻¹ at 1 A g	1 A g ⁻¹	Lu et al. ⁸
9	CC/ NiCo ₂ S ₄ @Zn–Ni–Co–S	2668 F g ⁻¹	1 A g ⁻¹	Peng et al. ⁹
10	NiCo ₂ S ₄ @rGO	2418 F g ⁻¹	1A g ⁻¹	Zhao et al. ¹⁰
11	NiCo ₂ S ₄ @2D-Carbyne nanohybrid	2507 F g ⁻¹	1 A g ⁻¹	Dhandapani et al. ¹¹

12	NiCo ₂ S ₄ /Co _x S _y	7218 F/g	2 A/g	This work.
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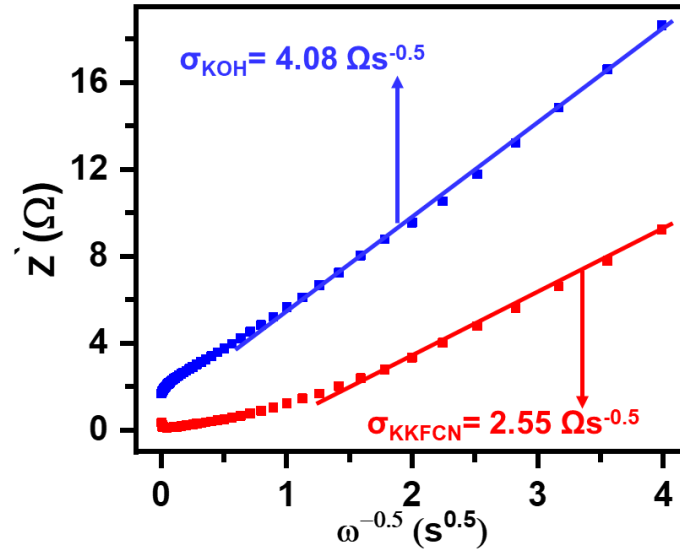


Figure S8: The Warburg factor σ with or without redox additive electrolyte for NCS/CS electrode.

S3: Specific capacitance, power density, and energy density calculations of solid-state supercapacitor device.

The specific capacitance of a solid-state symmetric supercapacitor device is calculated using equation S2,

$$C_s = \frac{I\Delta t_d}{m\Delta V} \text{ (F/g)}, \quad (\text{S2})$$

where I/m is the current density of the device. Additionally, the energy density and power density of the device were also calculated at different current densities using the following equation^{S3, S4}

$$E = \frac{1}{2} C_s (\Delta V)^2 \text{ (Wh/Kg)}, \quad (\text{S3})$$

$$P = 3600 \frac{E}{\Delta t_d} \text{ (W/Kg)}, \quad (\text{S4})$$

Table S3: Comparison table NCS/CS symmetric supercapacitor device with other previously reported devices.

S.No	Composition	Capacitance	Current density	Reference
1	NiCo ₂ S ₄ /20rGO//AC	92 F/g	5 A/g	Zhao et al. ¹²
2	NiCo ₂ S ₄ /PANI//AC	130 F/g	4 A/g	He et al. ¹³
3	NiCo ₂ S ₄ @PANI/CF//graphene/CF	182 F/g	5 A/g	Liu et al. ¹⁴
4	NiCo ₂ S ₄ /Co ₉ S ₈ HSs//AC	196 F/g	5 A/g	Han et al. ¹⁵
5	P doped Co–Ni–S//AC	155.4 F/g	5 A/g	Meng et al. ¹⁶
6	NiCo ₂ S ₄ @NiCo ₂ S ₄ //AC	83 F/g	4 A/g	Rong et al. ¹⁷
7	NiCo ₂ S ₄ @GR//AC	120 F/g	4 A/g	Xiao et al. ¹⁸
8	PNTs@ NiCo ₂ S ₄ //PNTs@ NiCo ₂ S ₄	165 F/g	5 A/g	Zhang et al. ¹⁹
9	NiCo ₂ S ₄ @PPy//AC	1.528 mAh/cm ²	5 mA/cm ²	Chen et al. ²⁰
10	NiCo ₂ S ₄ /Co _x S _y	380 F/g	1 A/g	This work

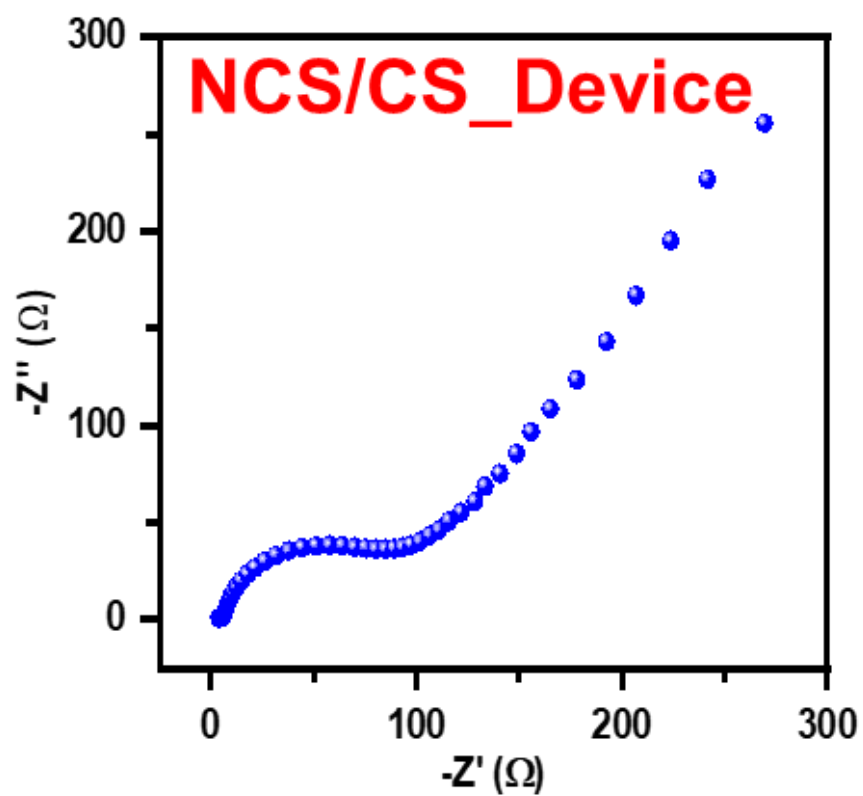


Figure S9: EIS spectra of NCS/CS symmetric supercapacitor device.

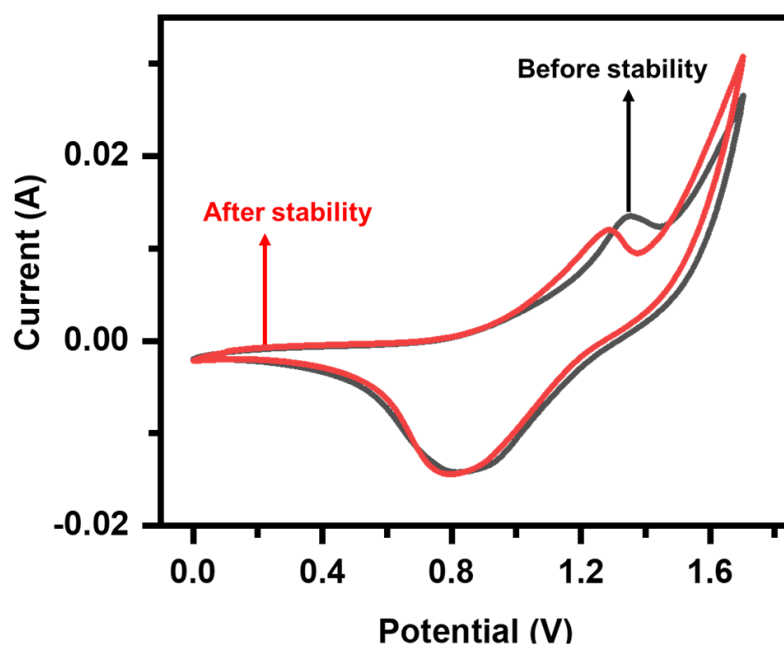


Figure S10: CV curve of the device before and after stability measurements.

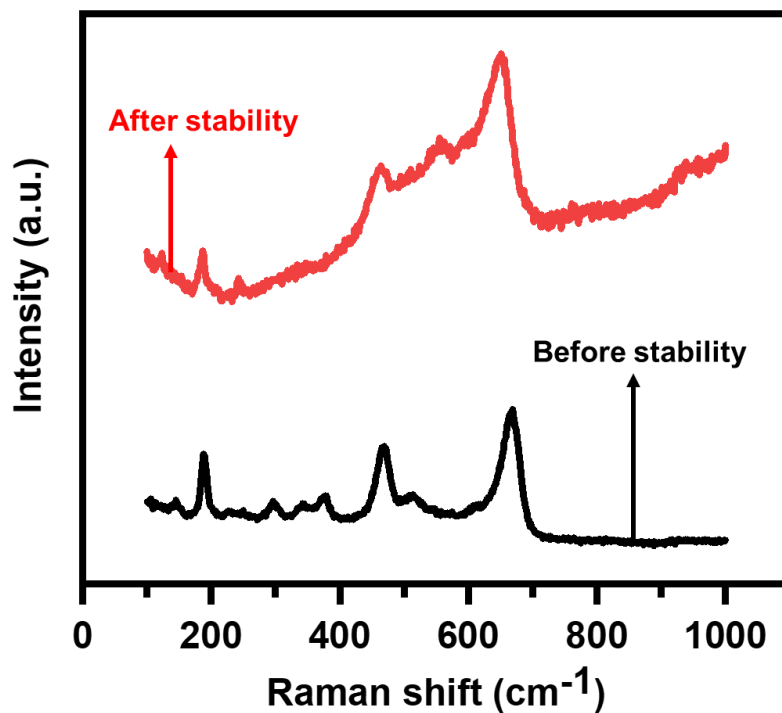


Figure S11: Raman Spectrum of the NCS/CS device before and after stability measurements.

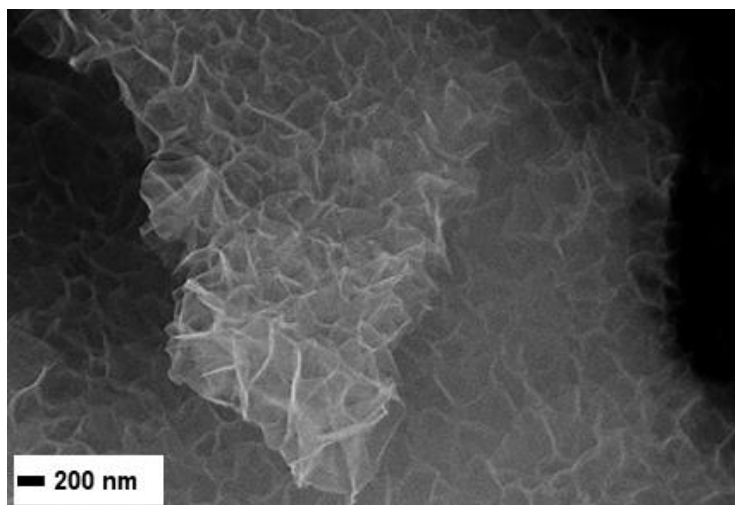


Figure S12: SEM image of NCS/CS complex after stability measurements.

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